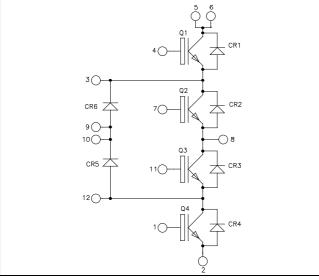
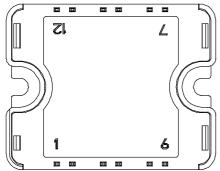


Three level inverter Trench + Field Stop IGBT3 Power Module







All multiple inputs and outputs must be shorted together 5/6; 9/10

Uninterruptible Power Supplies

 $V_{CES} = 600V$

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- **RoHS Compliant**

O1 to O4 Absolute maximum ratings

VI to VIIIosofate maximum ratings									
Symbol	Parameter		Max ratings	Unit					
V_{CES}	Collector - Emitter Breakdown Voltage		600	V					
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	32						
I_{C}	$T_{\rm C}$ =		20	A					
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	40						
V_{GE}	Gate – Emitter Voltage		±20	V					
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	62	W					
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150$ °C	40A @ 550V						

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
		$I_C = 20A$ $T_j = 150$ °C	$T_j = 150$ °C		1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 300 \mu A$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				300	nA

Q1 to Q4 Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		1100		
Coes	Output Capacitance	$V_{CE} = 25V$		70		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		35		
Q_{G}	Gate charge	V_{GE} =±15V, I_{C} =20A V_{CE} =300V		0.2		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		110		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 20A$		200		
$T_{\rm f}$	Fall Time	$R_G = 12\Omega$		40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		120		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		50		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 20A$		250		
$T_{\rm f}$	Fall Time	$R_G = 12\Omega$		60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.11		mJ
Lon	Turn-on Switching Energy	$V_{\text{Bus}} = 300 \text{V}$ $T_{\text{j}} = 150^{\circ} \text{C}$		0.2		1113
E_{off}	Turn-off Switching Energy	$I_C = 20A$ $T_j = 25^{\circ}C$		0.5		mJ
2011	Tam on Switching Energy	$R_G = 12\Omega \qquad T_j = 150^{\circ}C$		0.7		1110
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 360V$ $t_p \le 6\mu s$; $T_1 = 150^{\circ}C$		100		A
R_{thJC}	Junction to Case Thermal Resistance				2.4	°C/W

2 - 7



CR1 to CR6 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V	
I_{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 350	μΑ	
I_{F}	DC Forward Current		$T_1 = 130 \text{ C}$ $T_2 = 80 \text{ C}$		20	330	A	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 20A$	$T_i = 25^{\circ}C$		1.6	2	V	
V _F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		\ \ \	
t _{rr}	Reverse Recovery Time	$I_F = 20A$ $V_R = 300V$ $di/dt = 1600A/us$	$T_j = 25$ °C		100		ns μC	
v _{rr}			$T_{j} = 150^{\circ}C$		150			
Q _{rr}	Reverse Recovery Charge		$T_j = 25$ °C		1.1			
Qrr			$T_{i} = 150^{\circ}C$		2.3		μС	
E_{rr}	Reverse Recovery Energy	Payarsa Pagayary Engray	1	$T_j = 25$ °C		0.23		mJ
\mathbf{L}_{rr}			$T_{\rm j} = 150^{\circ}{\rm C}$		0.50		1113	
R_{thJC}	Junction to Case Thermal Resistance					3.25	°C/W	

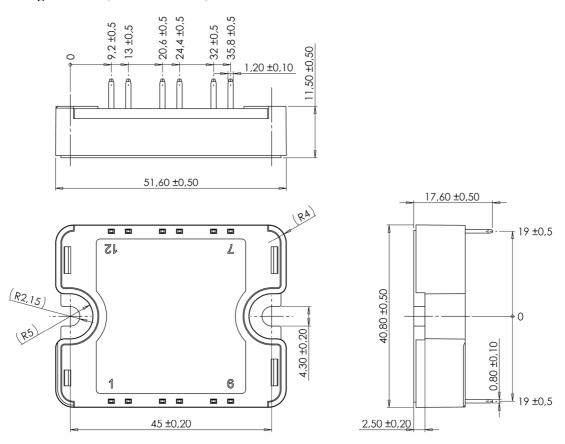
Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range			-40		125	°C
T_{C}	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

3 - 7



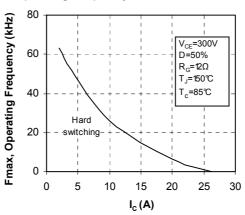
SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Q1 to Q4 Typical performance curve

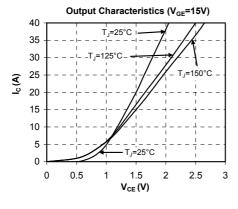
Operating Frequency vs Collector Current

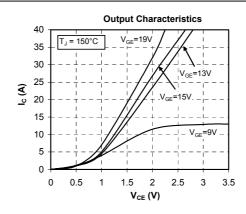


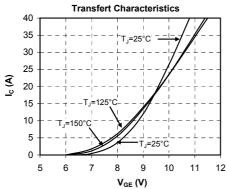
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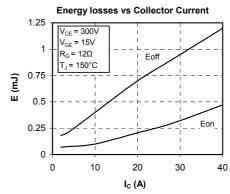
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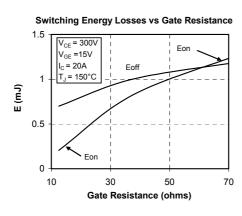


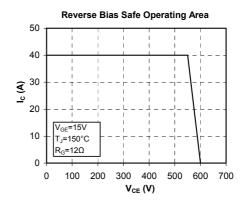


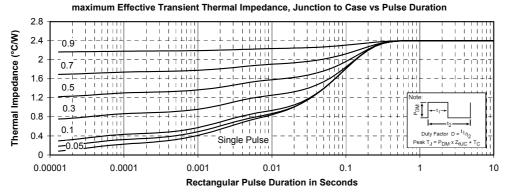






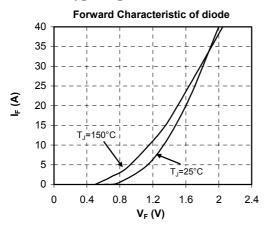




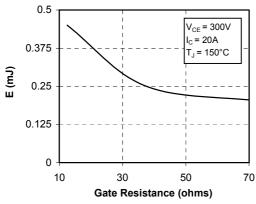




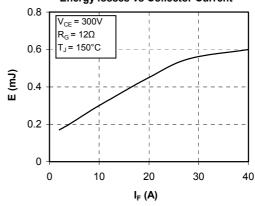
CR1 to CR6 Typical performance curve



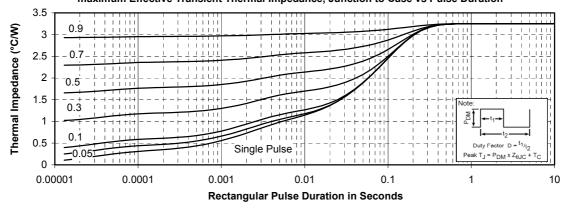
Switching Energy Losses vs Gate Resistance



Energy losses vs Collector Current



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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